



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

**SOT-89-3L Plastic-Encapsulate Transistors**

**PXT8050** TRANSISTOR (NPN)

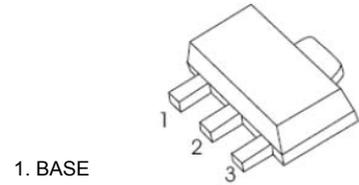
**SOT-89-3L**

**FEATURES**

- Compliment to PXT8550

**MARKING: Y1**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**



1. BASE
2. COLLECTOR
3. EMITTER

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	1.5	A
P <sub>C</sub>	Collector Power dissipation	0.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

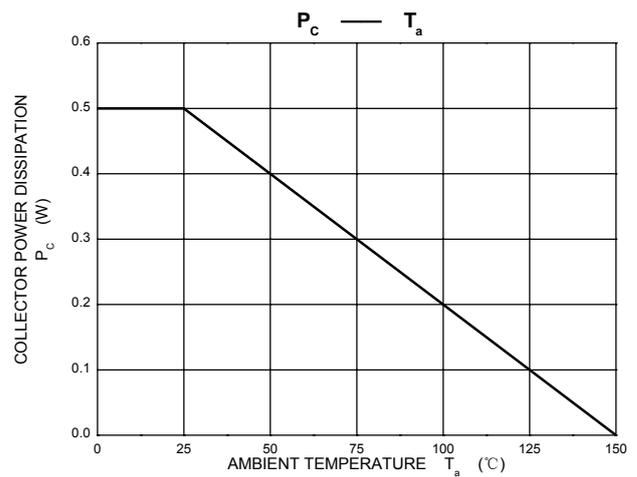
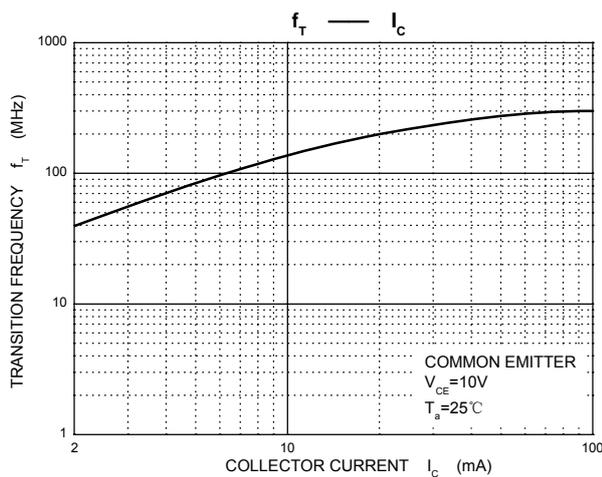
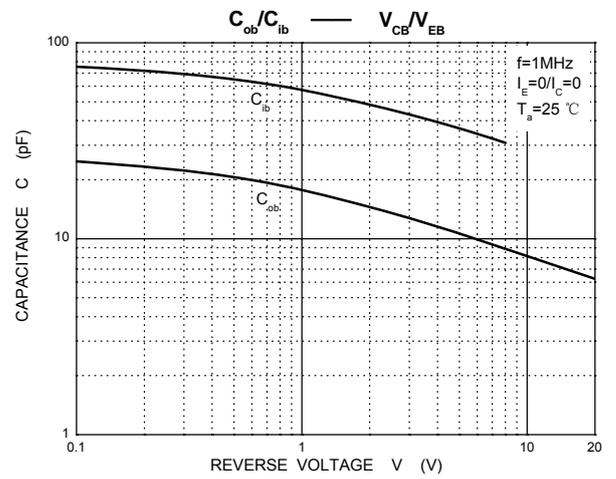
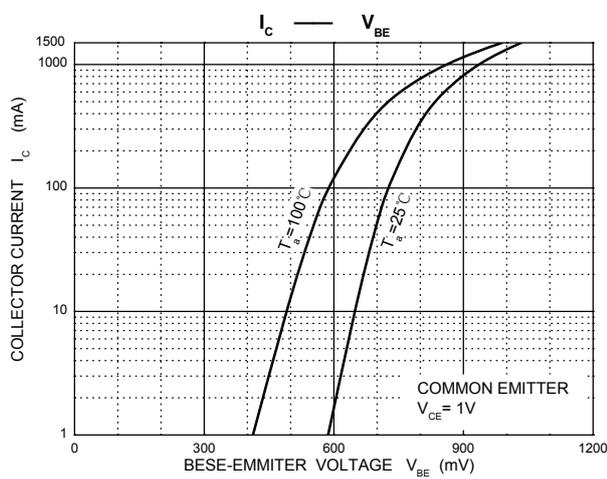
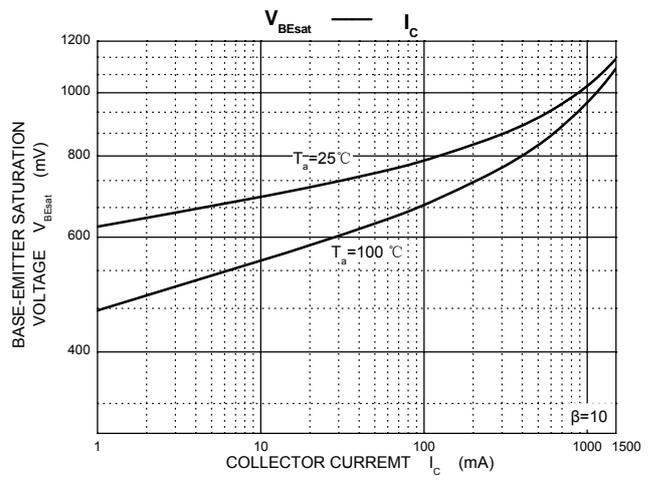
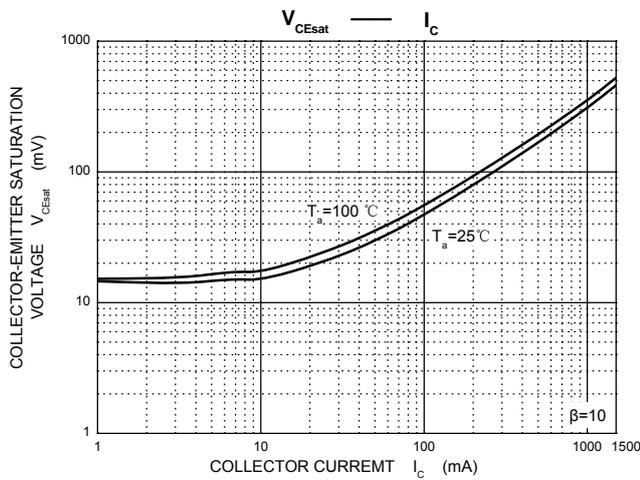
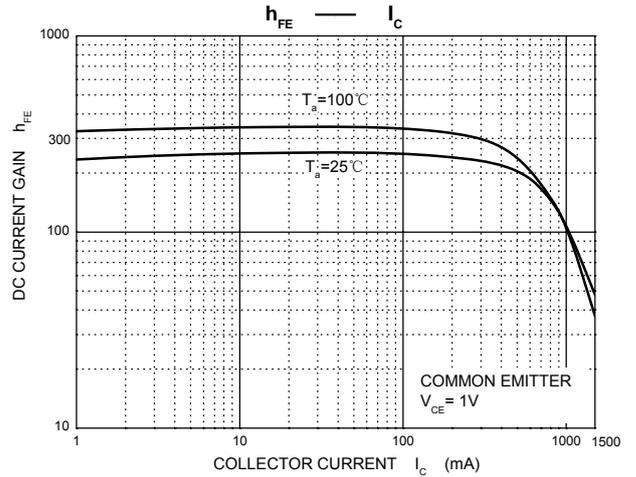
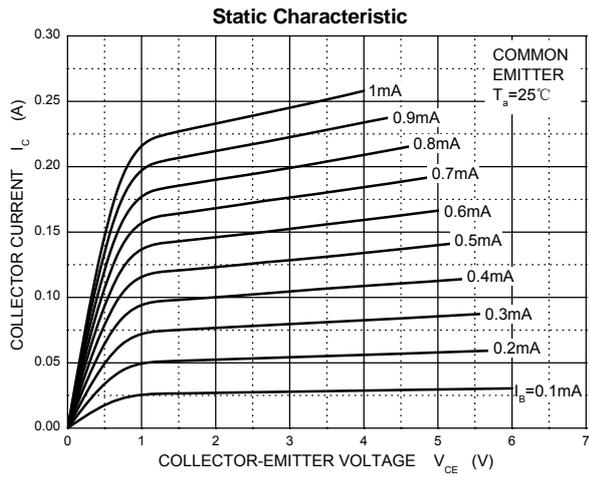
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =0.1mA, I <sub>B</sub> =0	25			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =20V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA	85		400	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =800mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =800mA, I <sub>B</sub> =80mA			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =800mA, I <sub>B</sub> =80mA			1.2	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA			1	V
Base-emitter positive favor voltage	V <sub>BEF</sub>	I <sub>B</sub> =1A			1.55	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA, f=30MHz	100			MHz
output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			15	pF

**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

# Typical Characteristics

# PXT8050



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Bipolar Transistors - BJT category](#):*

*Click to view products by [Changjiang manufacturer](#):*

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NJVMJD148T4G](#) [NTE123AP-10](#) [NTE153MCP](#) [NTE16](#)  
[NTE195A](#) [NTE92](#) [C4460](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC2712S-GR,LF](#) [2SC5488A-TL-H](#)  
[2SD2150T100R](#) [SP000011176](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC2412KT146S](#) [2SD1816S-TL-E](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#)  
[MJE340](#) [US6T6TR](#) [NJL0281DG](#) [732314D](#) [CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [IMZ2AT108](#) [UMX21NTR](#) [MCH6102-TL-E](#)  
[NJL0302DG](#) [2N3583](#) [30A02MH-TL-E](#) [NSV40301MZ4T1G](#) [NTE13](#) [NTE26](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [STX83003-AP](#)